Abstract
Microwave power transistors play key role in today's wireless communication, necessary for virtually all major aspects of human activities from entertainment, business to military. HEMT is widely used due to its high speed and power amplification capabilities. The paper proposes a current Model for short channel HEMT to evaluate its sensitivity to illumination to find its application in optical monolithic microwave integrated circuits (OMMIC).

Reference

- Noor Muhammad Memon “Modeling Techniques of Submicron GaAs MESFETs and HEMTs” Thesis Department of electronic engineering faculty of engineering and applied sciences Muhammad Ali Jinnah university Islamabad Campus, 2008.

Index Terms

Computer Science Wireless

Key words

2-DEG Schottky Junction
Current Model for Short channel Illuminated Gallium Nitride HEMT

detectors
   Photo voltage

   short channel

   Gallium Nitride

   OMMIC